



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-323 封装二极管/SOD-323 Plastic-Encapsulate Diodes

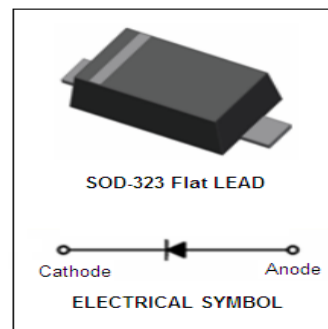
SD103AWS/SD103BWS/SD103CWS (SCHOTTKY DIODES)

特点/Features :

- 正向导通电压低；
- 环保护结构提供瞬态保护；
- 极小的恢复时间；
- 极小的反向电容；

用途/Applications :

高速开关电路。



极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}				
Working Peak	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Repetitive Peak Forward Current (@t≤1S)	I_{FSM}	1.5			A
Power Dissipation	P_d	200			mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	300			°C/mW
Storage Temperature	Tstg	-65~125			°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=100 \mu A$	40			V
SD103AWS		$I_R=100 \mu A$	30			
SD103BWS		$I_R=100 \mu A$	20			
Forward Voltage	V_F	$I_F=20mA$			0.37	V
		$I_F=200mA$			0.60	V
Reverse Current	I_{RM}	$V_R=30V$			5.0	μA
SD103AWS		$V_R=30V$				
SD103BWS		$V_R=30V$				
Capacitance Between Terminals	C_T	$V_R=0V, f=1.0MHz$			50	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=200mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$		10		nS

印章/ Marking:

型号	SD103AWS	SD103BWS	SD103CWS
印章	S4	S5	S6



典型特性曲线图/Typical Characteristics

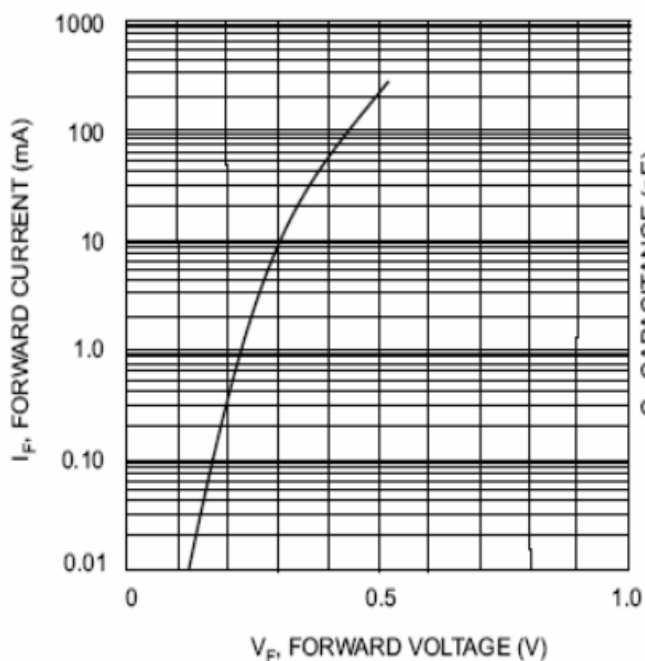


Fig. 1 Typical Forward Characteristics

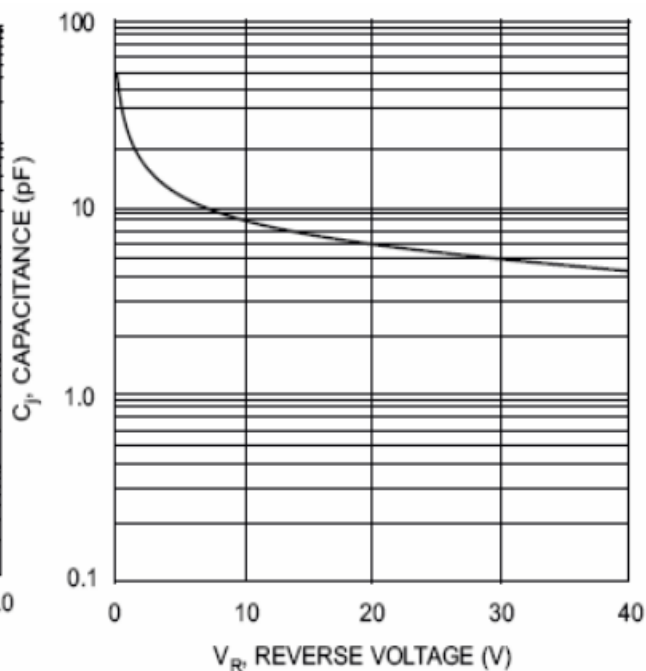


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage